

We Claim:

1. A device for producing at least one SiC single crystal, comprising:

a crucible and a heater device configured outside of said crucible;

said crucible having a crucible inner zone, at least one storage area for holding a stock of solid SiC, and at least one crystal area for holding at least one SiC seed crystal onto which an SiC single crystal grows;

said crucible having a side that faces said crucible inner zone;

said side being lined with a foil that includes a material selected from the group consisting of tantalum, tungsten, niobium, molybdenum, rhenium, iridium, ruthenium, hafnium, and zirconium.

2. The device according to claim 1, wherein said foil has a thickness of up to 200  $\mu\text{m}$ .

3. The device according to claim 2, wherein said crucible is at least substantially made from graphite.

4. The device according to claim 1, wherein said crucible is at least substantially made from graphite.
5. The device according to claim 1, wherein said heater device is an inductive heater device.
6. The device according to claim 1, wherein said crucible has a double-walled design.

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